Alex Hamilton

List of Publications by Year in Descending Order

202 papers	4,400 citations	34 h-index	58 g-index
242 ext. papers	5,101 ext. citations	4.7 avg, IF	5.16 L-index

#	Paper	IF	Citations
202	Optimizing topological switching in confined 2D-Xene nanoribbons via finite-size effects. *Applied Physics Reviews*, **2022**, 9, 011411	17.3	1
201	Understanding the Role of Defective Phases on the Conductivity Behavior of Strained Epitaxial LaNiO3 Thin Films. *ACS Applied Electronic Materials*, **2022**, 4, 1196-1205	4	
200	Lightly strained germanium quantum wells with hole mobility exceeding one million. *Applied Physics Letters*, **2022**, 120, 122104	3.4	3
199	Spin-Momentum Locking Induced Anisotropic Magnetoresistance in Monolayer WTe. *Nano Letters*, **2021**, 21, 9005-9011	11.5	0
198	Theory of hole-spin qubits in strained germanium quantum dots. *Physical Review B*, **2021**, 103,	3.3	8
197	Optimal operation points for ultrafast, highly coherent Ge hole spin-orbit qubits. *Npj Quantum Information*, **2021**, 7,	8.6	9
196	Electron□ole superfluidity in strained Si/Ge type II heterojunctions. *Npj Quantum Materials*, **2021**, 6,	5	3
195	Near-Field Excited Archimedean-like Tiling Patterns in Phonon-Polaritonic Crystals. *ACS Nano*, **2021**, 15, 9134-9142	16.7	8
194	Generating a Topological Anomalous Hall Effect in a Nonmagnetic Conductor: An In-Plane Magnetic Field as a Direct Probe of the Berry Curvature. *Physical Review Letters*, **2021**, 126, 256601	7.4	2
193	Anodic oxidation of epitaxial superconductor-semiconductor hybrids. *Physical Review Materials*, **2021**, 5,	3.2	2
192	New signatures of the spin gap in quantum point contacts. *Nature Communications*, **2021**, 12, 5	17.4	4
191	High electron mobility and low noise quantum point contacts in an ultra-shallow all-epitaxial metal gate GaAs/AlxGa1□As heterostructure. *Applied Physics Letters*, **2021**, 119, 063105	3.4	1
190	Geometric Control of Universal Hydrodynamic Flow in a Two-Dimensional Electron Fluid. *Physical Review X*, **2021**, 11,	9.1	1
189	Signatures of quantum mechanical Zeeman effect in classical transport due to topological properties of two-dimensional spin-32 holes. *Physical Review B*, **2020**, 101,	3.3	3
188	Experimental conditions for the observation of electron-hole superfluidity in GaAs heterostructures. *Physical Review B*, **2020**, 101,	3.3	7
187	Nonlinear spin filter for nonmagnetic materials at zero magnetic field. *Physical Review B*, **2020**, 102,	3.3	1
186	Improving reproducibility of quantum devices with completely undoped architectures. *Applied Physics Letters*, **2020**, 117, 183101	3.4	4

185	Two-dimensional lateral surface superlattices in GaAs heterostructures with independent control of carrier density and modulation potential. *Applied Physics Letters*, **2020**, 117, 032102	3.4	1
184	Three-dimensional electron-hole superfluidity in a superlattice close to room temperature. *Physical Review B*, **2020**, 102,	3.3	2
183	Quantum Anomalous Hall Effect in Magnetic Doped Topological Insulators and Ferromagnetic Spin-Gapless Semiconductors-A Perspective Review. *Small*, **2020**, 16, e1904322	11	13
182	g-factor and well-width fluctuations as a function of carrier density in the two-dimensional hole accumulation layer of transfer-doped diamond. *Physical Review B*, **2019**, 99,	3.3	8
181	A room-temperature ferroelectric semimetal. *Science Advances*, **2019**, 5, eaax5080	14.3	68
180	Antisymmetric magnetoresistance in van der Waals FeGeTe/graphite/FeGeTe trilayer heterostructures. *Science Advances*, **2019**, 5, eaaw0409	14.3	57
179	G-factor and well width variations for the two-dimensional hole gas in surface conducting diamond. *Applied Physics Letters*, **2018**, 112, 042102	3.4	15
178	Thickness-dependent electronic structure in WTe2 thin films. *Physical Review B*, **2018**, 98,	3.3	15
177	Multiband Mechanism for the Sign Reversal of Coulomb Drag Observed in Double Bilayer Graphene Heterostructures. *Physical Review Letters*, **2018**, 121, 036601	7.4	5
176	Spin and orbital structure of the first six holes in a silicon metal-oxide-semiconductor quantum dot. *Nature Communications*, **2018**, 9, 3255	17.4	26
175	Electrical Control of the Zeeman Spin Splitting in Two-Dimensional Hole Systems. *Physical Review Letters*, **2018**, 121, 077701	7.4	14
174	Strong Spin-Orbit Contribution to the Hall Coefficient of Two-Dimensional Hole Systems. *Physical Review Letters*, **2018**, 121, 087701	7.4	13
173	Spin□rbit coupling in silicon for electrons bound to donors. *Npj Quantum Information*, **2018**, 4,	8.6	9
172	Spin-orbit interactions in inversion-asymmetric two-dimensional hole systems: A variational analysis. *Physical Review B*, **2017**, 95,	3.3	29
171	Zero-Energy Modes from Coalescing Andreev States in a Two-Dimensional Semiconductor-Superconductor Hybrid Platform. *Physical Review Letters*, **2017**, 119, 176805	7.4	129
170	Spin blockade in hole quantum dots: Tuning exchange electrically and probing Zeeman interactions. *Physical Review B*, **2017**, 95,	3.3	21
169	Mechanisms for Strong Anisotropy of In-Plane g-Factors in Hole Based Quantum Point Contacts. *Physical Review Letters*, **2017**, 119, 116803	7.4	12
168	Detection and Control of Spin-Orbit Interactions in a GaAs Hole Quantum Point Contact. *Physical Review Letters*, **2017**, 118, 146801	7.4	12

167	Electrical control of the sign of the g factor in a GaAs hole quantum point contact. *Physical Review B* , **2016**, 94,	3.3	9
166	Manifestation of a non-Abelian Berry phase in a p-type semiconductor system. *Physical Review B*, **2016**, 93,	3.3	10
165	Double-layer-gate architecture for few-hole GaAs quantum dots. *Nanotechnology*, **2016**, 27, 334001	3.4	4
164	Spin Control Without Magnetic Fields. *Physics Magazine*, **2016**, 9,	1.1	9
163	Anisotropic Pauli Spin Blockade of Holes in a GaAs Double Quantum Dot. *Nano Letters*, **2016**, 16, 7685-7689	11.5	30
162	Strong and Tunable Spin-Orbit Coupling in a Two-Dimensional Hole Gas in Ionic-Liquid Gated Diamond Devices. *Nano Letters*, **2016**, 16, 3768-73	11.5	36
161	Using light and heat to controllably switch and reset disorder configuration in nanoscale devices. *Physical Review B*, **2015**, 91,	3.3	5
160	Landau level spin diode in a GaAs two dimensional hole system. *New Journal of Physics*, **2015**, 17, 033035	2.9	4
159	Pauli Spin Blockade of Heavy Holes in a Silicon Double Quantum Dot. *Nano Letters*, **2015**, 15, 7314-8	11.5	48
158	Dependence of the 0.7 anomaly on the curvature of the potential barrier in quantum wires. *Physical Review B*, **2015**, 91,	3.3	7
157	Bottom-up assembly of metallic germanium. *Scientific Reports*, **2015**, 5, 12948	4.9	18
156	Transverse magnetic focussing of heavy holes in a (100) GaAs quantum well. *Semiconductor Science and Technology*, **2015**, 30, 102001	1.8	1
155	Fabrication and characterisation of gallium arsenide ambipolar quantum point contacts. *Applied Physics Letters*, **2015**, 106, 183504	3.4	5
154	Hybrid architecture for shallow accumulation mode AlGaAs/GaAs heterostructures with epitaxial gates. *Applied Physics Letters*, **2015**, 106, 012105	3.4	7
153	Spin-orbit interaction in a two-dimensional hole gas at the surface of hydrogenated diamond. *Nano Letters*, **2015**, 15, 16-20	11.5	34
152	Radio-frequency reflectometry on an undoped AlGaAs/GaAs single electron transistor. *Applied Physics Letters*, **2014**, 104, 012114	3.4	5
151	Transport in disordered monolayer MoS2 nanoflakes--evidence for inhomogeneous charge transport. *Nanotechnology*, **2014**, 25, 375201	3.4	23
150	Probing the spin states of a single acceptor atom. *Nano Letters*, **2014**, 14, 1492-6	11.5	25

149	**2014**,		1
148	Excitonic superfluidity and screening in electron-hole bilayer systems. *Physical Review B*, **2014**, 89,	3.3	42
147	Noncollinear paramagnetism of a GaAs two-dimensional hole system. *Physical Review Letters*, **2014**, 113, 236401	7.4	8
146	Determining the stability and activation energy of Si acceptors in AlGaAs using quantum interference in an open hole quantum dot. *Physical Review B*, **2014**, 89,	3.3	1
145	Is it the boundaries or disorder that dominates electron transport in semiconductor billiards. *Fortschritte Der Physik*, **2013**, 61, 332-347	5.7	10
144	High-temperature superfluidity in double-bilayer graphene. *Physical Review Letters*, **2013**, 110, 146803	7.4	131
143	Influence of surface states on quantum and transport lifetimes in high-quality undoped heterostructures. *Physical Review B*, **2013**, 87,	3.3	17
142	Single hole transport in a silicon metal-oxide-semiconductor quantum dot. *Applied Physics Letters*, **2013**, 103, 163508	3.4	20
141	A study of transport suppression in an undoped AlGaAs/GaAs quantum dot single-electron transistor. *Journal of Physics Condensed Matter*, **2013**, 25, 505302	1.8	4
140	Using a tunable quantum wire to measure the large out-of-plane spin splitting of quasi two-dimensional holes in a GaAs nanostructure. *Nano Letters*, **2013**, 13, 148-52	11.5	21
139	Scaling of the Kondo zero-bias peak in a hole quantum dot at finite temperatures. *Physical Review B* , **2013**, 87,	3.3	11
138	Ultra-shallow quantum dots in an undoped GaAs/AlGaAs two-dimensional electron gas. *Applied Physics Letters*, **2013**, 102, 103507	3.4	14
137	QUANTUM GLASS TRANSITION AT FINITE TEMPERATURE IN TWO-DIMENSIONAL ELECTRON LAYERS. *International Journal of Modern Physics B*, **2013**, 27, 1347004	1.1	
136	Extreme sensitivity of the spin-splitting and 0.7 anomaly to confining potential in one-dimensional nanoelectronic devices. *Nano Letters*, **2012**, 12, 4495-502	11.5	18
135	Stacking of 2D electron gases in Ge probed at the atomic level and its correlation to low-temperature magnetotransport. *Nano Letters*, **2012**, 12, 4953-9	11.5	17
134	Fabrication and characterization of ambipolar devices on an undoped AlGaAs/GaAs heterostructure. *Applied Physics Letters*, **2012**, 100, 052101	3.4	30
133	Impact of small-angle scattering on ballistic transport in quantum dots. *Physical Review Letters*, **2012**, 108, 196807	7.4	24
132	Origin of gate hysteresis in p-type Si-doped AlGaAs/GaAs heterostructures. *Physical Review B*, **2012**, 86,	3.3	12

131	Probing the sensitivity of electron wave interference to disorder-induced scattering in solid-state devices. *Physical Review B*, **2012**, 85,	3.3	6
130	Charge transport by modulating spin-orbit gauge fields for quasi-one-dimensional holes. *Applied Physics Letters*, **2011**, 98, 152101	3.4	1
129	Resistively detected nuclear magnetic resonance in n- and p-type GaAs quantum point contacts. *Nano Letters*, **2011**, 11, 3147-50	11.5	24
128	(100) GaAs/AlxGa1□As heterostructures for Zeeman spin splitting studies of hole quantum wires. *Journal of Crystal Growth*, **2011**, 323, 48-51	1.6	
127	Compressibility measurements of quasi-one-dimensional quantum wires. *Physical Review Letters*, **2011**, 107, 126801	7.4	10
126	Observation of the Kondo effect in a spin-3/2 hole quantum dot. *Physical Review Letters*, **2011**, 107, 076805	7.4	23
125	Overlapping-Gate Architecture for Silicon Hall Bar MOSFET Devices in the Low Electron Density and High Magnetic Field Regime. *Materials Science Forum*, **2011**, 700, 93-95	0.4	
124	Electrometry using the quantum Hall effect in a bilayer two-dimensional electron system. *Applied Physics Letters*, **2010**, 96, 212102	3.4	5
123	Field-orientation dependence of the Zeeman spin splitting in (In,Ga)As quantum point contacts. *Physical Review B*, **2010**, 81,	3.3	17
122	Anomalous transport in mesoscopic inhomogeneous two-dimensional electron systems at low temperature. *Physical Review B*, **2010**, 82,	3.3	4
121	Overlapping-gate architecture for silicon Hall bar field-effect transistors in the low electron density regime. *Applied Physics Letters*, **2010**, 97, 152102	3.4	5
120	AlGaAs/GaAs single electron transistor fabricated without modulation doping. *Applied Physics Letters*, **2010**, 96, 112104	3.4	20
119	Observation of orientation- andk-dependent Zeeman spin-splitting in hole quantum wires on (100)-oriented AlGaAs/GaAs heterostructures. *New Journal of Physics*, **2010**, 12, 033043	2.9	25
118	Velocity-modulation control of electron-wave propagation in graphene. *Physical Review B*, **2010**, 81,	3.3	95
117	Fabrication and characterization of an induced GaAs single hole transistor. *Applied Physics Letters*, **2010**, 96, 092103	3.4	20
116	Origin of the hysteresis in bilayer two-dimensional systems in the quantum Hall regime. *Physical Review B*, **2010**, 82,	3.3	3
115	Piezoelectric rotator for studying quantum effects in semiconductor nanostructures at high magnetic fields and low temperatures. *Review of Scientific Instruments*, **2010**, 81, 113905	1.7	17
114	Ground-plane screening of Coulomb interactions by a nearby two-dimensional system. *Physica E: Low-Dimensional Systems and Nanostructures*, **2010**, 42, 1228-1231	3	

113	Crystallographic anisotropy of the Zeeman splitting in 1D hole quantum wires. *Physica E: Low-Dimensional Systems and Nanostructures*, **2010**, 42, 967-970	3	
112	Radio-frequency reflectometryÂ fast and sensitive measurement method for two-dimensional systems. *Physica E: Low-Dimensional Systems and Nanostructures*, **2010**, 42, 1192-1195	3	1
111	Ballistic induced hole quantum wires fabricated on a (100)-oriented AlGaAs/GaAs heterostructure. *Physica E: Low-Dimensional Systems and Nanostructures*, **2010**, 42, 1111-1113	3	2
110	Ground-plane screening of Coulomb interactions in two-dimensional systems: How effectively can one two-dimensional system screen interactions in another. *Physical Review B*, **2009**, 80,	3.3	12
109	Quantum tunnelling and hopping between metallic domains in disordered two-dimensional mesoscopic electron systems. *Journal of Physics A: Mathematical and Theoretical*, **2009**, 42, 214012	2	1
108	The interplay between one-dimensional confinement and two-dimensional crystallographic anisotropy effects in ballistic hole quantum wires. *New Journal of Physics*, **2009**, 11, 043018	2.9	20
107	Role of background impurities in the single-particle relaxation lifetime of a two-dimensional electron gas. *Physical Review B*, **2009**, 80,	3.3	32
106	Measuring the Charge and Spin States of Electrons on Individual Dopant Atoms in Silicon. *Topics in Applied Physics*, **2009**, 169-182	0.5	1
105	Impact of long- and short-range disorder on the metallic behaviour of two-dimensional systems. *Nature Physics*, **2008**, 4, 55-59	16.2	35
104	Atomic-scale silicon device fabrication. *International Journal of Nanotechnology*, **2008**, 5, 352	1.5	25
103	DREAMS VERSUS REALITY: PLENARY DEBATE SESSION ON QUANTUM COMPUTING. *Fluctuation and Noise Letters*, **2008**, 08, C27-C51	1.2	
102	TUNNELING AND HOPPING BETWEEN DOMAINS IN THE METAL-INSULATOR TRANSITION IN TWO-DIMENSIONS. *International Journal of Modern Physics B*, **2008**, 22, 4565-4571	1.1	2
101	The 0.7 anomaly in one-dimensional hole quantum wires. *Journal of Physics Condensed Matter*, **2008** , 20, 164205	1.8	8
100	Effect of screening long-range Coulomb interactions on the metallic behavior in two-dimensional hole systems. *Physical Review B*, **2008**, 77,	3.3	14
99	Enhanced Zeeman splitting in Ga0.25In0.75As quantum point contacts. *Applied Physics Letters*, **2008** , 93, 012105	3.4	22
98	Electron-electron interactions in highly disordered two-dimensional systems. *Physical Review B*, **2008**, 77,	3.3	35
97	Radio-frequency reflectometry on large gated two-dimensional systems. *Review of Scientific Instruments*, **2008**, 79, 123901	1.7	10
96	Ohmic conduction of sub-10nm P-doped silicon nanowires at cryogenic temperatures. *Applied Physics Letters*, **2008**, 92, 052101	3.4	11

95	Confinement properties of a Ga0.25In0.75As/InP quantum point contact. *Physical Review B*, **2008**, 77,	3.3	13
94	0.7 Structure and zero bias anomaly in ballistic hole quantum wires. *Physical Review Letters*, **2008**, 100, 016403	7.4	26
93	Quantum transport in one-dimensional GaAs hole systems. *International Journal of Nanotechnology*, **2008**, 5, 318	1.5	1
92	0.7 Structure and zero bias anomaly in one-dimensional hole systems. *Physica E: Low-Dimensional Systems and Nanostructures*, **2008**, 40, 1501-1503	3	
91	Metallic behavior in low-disorder two-dimensional hole systems in the presence of long- and short-range disorder. *Physica E: Low-Dimensional Systems and Nanostructures*, **2008**, 40, 1599-1601	3	
90	Screening long-range Coulomb interactions in 2D hole systems using a bilayer heterostructure. *Physica E: Low-Dimensional Systems and Nanostructures*, **2008**, 40, 1700-1702	3	1
89	Realization of atomically controlled dopant devices in silicon. *Small*, **2007**, 3, 563-7	11	87
88	Atomically precise silicon device fabrication **2007**,		1
87	An improved process for fabricating high-mobility organic molecular crystal field-effect transistors. *Journal of Applied Physics*, **2007**, 102, 084511	2.5	7
86	Use of low-temperature Hall effect to measure dopant activation: Role of electron-electron interactions. *Physical Review B*, **2007**, 76,	3.3	6
85	Electronic properties of atomically abrupt tunnel junctions in silicon. *Physical Review B*, **2007**, 75,	3.3	28
84	One-dimensional conduction properties of highly phosphorus-doped planar nanowires patterned by scanning probe microscopy. *Physical Review B*, **2007**, 76,	3.3	32
83	The effect of temperature and gas flow on the physical vapour growth of mm-scale rubrene crystals for organic FETs **2007**,		3
82	Narrow, highly P-doped, planar wires in silicon created by scanning probe microscopy. *Nanotechnology*, **2007**, 18, 044023	3.4	23
81	Electrical Characterization of Ordered Si:P Dopant Arrays. *IEEE Nanotechnology Magazine*, **2007**, 6, 213-217	1.6	16
80	Single particle and momentum relaxation times in two-dimensional electron systems (updated May 14, 2008) **2007**,		1
79	Zeeman splitting in ballistic hole quantum wires. *Physical Review Letters*, **2006**, 97, 026403	7.4	75
78	Electric-field-induced charge noise in doped silicon: Ionization of phosphorus donors. *Applied Physics Letters*, **2006**, 88, 162117	3.4	1

77	Ballistic transport in induced one-dimensional hole systems. *Applied Physics Letters*, **2006**, 89, 092105	3.4	46
76	Fabrication of induced two-dimensional hole systems on (311)A GaAs. *Journal of Applied Physics*, **2006**, 99, 023707	2.5	25
75	Conductance quantization and the 0.7□e2□ conductance anomaly in one-dimensional hole systems. *Applied Physics Letters*, **2006**, 88, 012107	3.4	37
74	Controlled single electron transfer between Si:P dots. *Applied Physics Letters*, **2006**, 88, 192101	3.4	24
73	Influence of doping density on electronic transport in degenerate Si:P □doped layers. *Physical Review B*, **2006**, 73,	3.3	45
72	Superconductivity in metal-mixed ion-implanted polymer films. *Applied Physics Letters*, **2006**, 89, 152503	3.4	6
71	Electrically detected magnetic resonance in ion-implanted Si:P nanostructures. *Applied Physics Letters*, **2006**, 89, 182115	3.4	73
70	Ballistic transport in one-dimensional bilayer hole systems. *Physica E: Low-Dimensional Systems and Nanostructures*, **2006**, 34, 550-552	3	2
69	Scanning probe microscopy for silicon device fabrication. *Molecular Simulation*, **2005**, 31, 505-515	2	42
68	Fabrication and characterization of a 2D hole system a in novel (311)A GaAs SISFET. *Microelectronics Journal*, **2005**, 36, 327-330	1.8	2
67	Single atom Si nanoelectronics using controlled single-ion implantation. *Microelectronic Engineering* , **2005**, 78-79, 279-286	2.5	7
66	Scaling of coherent tunneling adiabatic passage in solid-state coherent quantum systems **2005**,		3
65	Donor activation and damage in Si□SiO2from low-dose, low-energy ion implantation studied via electrical transport in MOSFETs. *Semiconductor Science and Technology*, **2005**, 20, 363-368	1.8	12
64	The use of etched registration markers to make four-terminal electrical contacts to STM-patterned nanostructures. *Nanotechnology*, **2005**, 16, 2446-9	3.4	23
63	Single-shot readout with the radio-frequency single-electron transistor in the presence of charge noise. *Applied Physics Letters*, **2005**, 86, 143117	3.4	27
62	Interaction correction to the longitudinal conductivity and Hall resistivity in high-quality two-dimensional GaAs electron and hole systems. *Physical Review B*, **2005**, 72,	3.3	10
61	Evolution of the bilayer □1 quantum Hall state under charge imbalance. *Physical Review B*, **2005**, 71,	3.3	14
60	Electrical readout of a spin qubit without double occupancy. *Physical Review B*, **2005**, 71,	3.3	20

59	Observing sub-microsecond telegraph noise with the radio frequency single electron transistor. *Journal of Applied Physics*, **2004**, 96, 6827-6830	2.5	20
58	Effect of encapsulation temperature on Si:P δ-doped layers. *Applied Physics Letters*, **2004**, 85, 4953-4955	3.4	39
57	Maximizing the Hilbert space for a finite number of distinguishable quantum states. *Physical Review Letters*, **2004**, 92, 097901	7.4	49
56	Coherent electronic transfer in quantum dot systems using adiabatic passage. *Physical Review B*, **2004**, 70,	3.3	218
55	Weak localization in high-quality two-dimensional systems. *Physical Review B*, **2004**, 70,	3.3	46
54	Charge shelving and bias spectroscopy for the readout of a charge qubit on the basis of superposition states. *Physical Review B*, **2004**, 70,	3.3	13
53	Development and operation of the twin radio frequency single electron transistor for cross-correlated charge detection. *Journal of Applied Physics*, **2004**, 96, 4508-4513	2.5	15
52	Stability of the bilayer ν=1 quantum Hall state under charge imbalance. *Physica E: Low-Dimensional Systems and Nanostructures*, **2004**, 22, 40-43	3	1
51	Toward Atomic-Scale Device Fabrication in Silicon Using Scanning Probe Microscopy. *Nano Letters*, **2004**, 4, 1969-1973	11.5	128
50	Charge-based quantum computing using single donors in semiconductors. *Physical Review B*, **2004**, 69,	3.3	237
49	Dreams Versus Reality: Plenary Debate Session on Quantum Computing. *Quantum Information Processing*, **2003**, 2, 449-472	1.6	2
48	The twin radio frequency single electron transistor for correlated charge detection on microsecond time-scales. *Microelectronic Engineering*, **2003**, 67-68, 775-781	2.5	7
47	Double-island single-electron transistor for noise-suppressed detection of charge transfer. *Microelectronic Engineering*, **2003**, 67-68, 826-831	2.5	5
46	Single electron devices for simulating read-out in a solid state quantum computer. *Surface Science*, **2003**, 532-535, 1199-1203	1.8	1
45	Progress in silicon-based quantum computing. *Philosophical Transactions Series A, Mathematical, Physical, and Engineering Sciences*, **2003**, 361, 1451-71	3	49
44	Current suppression in a double-island single-electron transistor for detection of degenerate charge configurations of a floating double-dot. *Applied Physics Letters*, **2003**, 83, 4640-4642	3.4	6
43	Correlated charge detection for readout of a solid-state quantum computer. *Applied Physics Letters*, **2003**, 82, 577-579	3.4	29
42	Localisation in Strongly Interacting 2D GaAs Systems. *Physica Status Solidi (B): Basic Research*, **2002**, 230, 81-87	1.3	2

41	Exchange-driven bilayer-to-monolayer charge transfer in an asymmetric double-quantum-well. *Physica E: Low-Dimensional Systems and Nanostructures*, **2002**, 12, 304-306	3	2
40	The fate of quantum Hall extended states as B-0 and the possibility of a 2D metal. *Physica E: Low-Dimensional Systems and Nanostructures*, **2002**, 12, 646-649	3	3
39	Modelling of electrostatic gate operations in the Kane solid state quantum computer. *Microelectronics Journal*, **2002**, 33, 1053-1058	1.8	8
38	Density-dependent spin polarization in ultra-low-disorder quantum wires. *Physical Review Letters*, **2002**, 89, 246801	7.4	142
37	Encapsulation of phosphorus dopants in silicon for the fabrication of a quantum computer. *Applied Physics Letters*, **2002**, 81, 3197-3199	3.4	83
36	Magnetic susceptibility of the normal-superconducting transition in high-purity single-crystal uranium. *Physical Review B*, **2002**, 66,	3.3	4
35	Single-electron transistor architectures for charge motion detection in solid-state quantum computer devices. *Smart Materials and Structures*, **2002**, 11, 749-755	3.4	3
34	A self-aligned fabrication process for silicon quantum computer devices. *Nanotechnology*, **2002**, 13, 686-690	3.4	7
33	Localisation and the metal-insulator transition in two dimensions. *Physica B: Condensed Matter*, **2001**, 296, 21-31	2.8	13
32	Metallic behaviour and localisation in 2D GaAs hole systems. *Physica E: Low-Dimensional Systems and Nanostructures*, **2001**, 11, 161-166	3	3
31	Many-body spin-related phenomena in ultra low-disorder quantum wires. *Physical Review B*, **2001**, 63,	3.3	135
30	Metallic behavior in dilute two-dimensional hole systems. *Physical Review Letters*, **2001**, 87, 126802	7.4	27
29	Is there a true metallic state in two dimensions?. *Springer Proceedings in Physics*, **2001**, 735-738	0.2	
28	Uranium Superconductivity Redux. *Journal of Superconductivity and Novel Magnetism*, **2000**, 13, 833-835		6
27	Weak localization, hole-hole interactions, and the "Metal"-insulator transition in two dimensions. *Physical Review Letters*, **2000**, 84, 2489-92	7.4	90
26	Influence of Inversion Symmetry on the Metallic Behaviour in a Dilute Two-dimensional Hole System. *Australian Journal of Physics*, **2000**, 53, 523		2
25	Reentrant Insulator-Metal-Insulator Transition at B=0 in a Two-Dimensional Hole Gas. *Physical Review Letters*, **1999**, 82, 1542-1545	7.4	58
24	Anomalous integer quantum Hall states in coupled double quantum wells and the effect of Landau level broadening. *Journal of Physics Condensed Matter*, **1999**, 11, 3711-3728	1.8	

23	Metal-Insulator Transition at B=0 in a Dilute Two Dimensional GaAs-AlGaAs Hole Gas. *Physical Review Letters*, **1998**, 80, 1292-1295	7.4	219
22	Magnetization Instability in a Two-Dimensional System. *Physical Review Letters*, **1997**, 79, 4449-4452	7.4	49
21	Fabrication of high mobility in situ back-gated (311)A hole gas heterojunctions. *Applied Physics Letters*, **1997**, 70, 2750-2752	3.4	24
20	Enhanced g factors of a one-dimensional hole gas with quantized conductance. *Physical Review B*, **1997**, 55, R13409-R13412	3.3	44
19	The physics and fabrication of in situ back-gated (311)A hole gas heterojunctions. *Microelectronics Journal*, **1997**, 28, 795-801	1.8	1
18	Frictional drag between parallel two-dimensional electron gases in a perpendicular magnetic field. *Journal of Physics Condensed Matter*, **1996**, 8, L557-L562	1.8	38
17	Integer quantum Hall states in coupled double electron gas systems at mismatched carrier densities. *Journal of Physics Condensed Matter*, **1996**, 8, L311-L318	1.8	6
16	Measurements of a composite fermion split-gate. *Surface Science*, **1996**, 361-362, 71-74	1.8	5
15	Probing the band structure of a two-dimensional hole gas using a one-dimensional superlattice. *Physical Review B*, **1996**, 54, R14273-R14276	3.3	4
14	Fractional quantum Hall effect in bilayer two-dimensional hole-gas systems. *Physical Review B*, **1996** , 54, R5259-R5262	3.3	27
13	Measurements of a composite fermion split-gate device. *Physical Review B*, **1996**, 53, R7596-R7598	3.3	11
12	The growth of high mobility heterostructures on (311)B GaAs. *Microelectronics Journal*, **1995**, 26, 897-902	1.8	2
11	Transition from one- to two-subband occupancy in the 2DEG of back-gated modulation-doped GaAs-AlxGa1-xAs heterostructures. *Physical Review B*, **1995**, 51, 17600-17604	3.3	10
10	The fabrication of back-gated high electron mobility transistors a novel approach using MBE regrowth on an in situ ion beam patterned epilayer. *Journal of Crystal Growth*, **1993**, 127, 41-45	1.6	7
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